



**In the United States Patent and Trademark Office**

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|------------------|-----------------------------|---|-----------------------|
| Inventor:        | Aratani et al.              | ) | Examiner: R. McDonald |
|                  |                             | ) |                       |
| Serial No.:      | 09/429,719                  | ) |                       |
|                  |                             | ) | Group Unit: 1753      |
|                  |                             | ) |                       |
| Title:           | Thin Film Formation Use ... | ) |                       |
|                  |                             | ) |                       |
| Atty. Docket No. | 9792486-0100                | ) |                       |

Response "D" to First Non-Final Office Action After RCE Filing

**RECEIVED**  
FEB 22 2002  
TC 1700

In response to the Office Action dated 25 Oct. 2001, the applicants respond as follows.

Clean Copy of Claims

Please cancel claims 1, 7, 10-12, 14-16 and add new claims 17-24.

17. A method of forming a thin film comprising the step of: forming an AgPd alloy thin film using a sputtering target material, the AgPd alloy thin film comprising Pd in an amount ranging from 0.5 to 4.9 atomic % and Cu in an amount ranging from 0.1 to 3.5 atomic %; and irradiating an information recording layer with a light beam having a wavelength.

18. The method of claim 17, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms.

19 The method of claim 17, wherein the wavelength is less than or equal to 650 nm.

20. The method of claim 17, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms; and wherein the wavelength is less than or equal to 650 nm.

21. A method of forming a thin film comprising the step of: forming an AgPdTi alloy thin film using a sputtering target material, the AgPdTi alloy comprising Pd in an amount ranging from 0.1 to 1.5 atomic %, Ti in an amount ranging from 0.1 to 2.9 atomic %, and Cu in an amount ranging from 0.1 to 3.5 atomic %.

22. The method of claim 21, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms.

23. The method of claim 21, wherein the wavelength is less than or equal to 650 nm.

24. The method of claim 21, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms; and wherein the wavelength is less than or equal to 650 nm.